

Title (en)
INTEGRATED SEMICONDUCTOR PRODUCT COMPRISING A METAL-INSULATOR-METAL CAPACITOR

Title (de)
INTEGRIERTES HALBLEITERPRODUKT MIT METALL-ISOLATOR-METALL-KONDENSATOR

Title (fr)
PRODUIT SEMI-CONDUCTEUR INTEGRE A CONDENSATEUR METAL-ISOLANT-METAL

Publication
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Application
EP 02792906 A 20021205

Priority
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• EP 0213804 W 20021205

Abstract (en)
[origin: WO03054934A1] To produce an integrated semiconductor product comprising an integrated metal-insulator-metal capacitor, a dielectric auxiliary layer (6) is first deposited on a first electrode (2, 3, 5). Said auxiliary layer (6) is then opened over the first electrode (15). A dielectric layer (7) is then created, onto which the stack (8, 9, 10) of metal strips for the second electrode is applied. The metal-insulator-metal capacitor is subsequently patterned using conventional etching technology. This allows the production of dielectric capacitor layers comprising freely selectable materials of any thickness. The particular advantage of the invention is that the etching of vias can be carried out in a significantly simpler manner than in prior art, as it is not necessary to etch through the remaining dielectric capacitor layer over the metal strips.

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H01L 21/76838 (2013.01 - US)

Citation (search report)
See references of WO 03054934A1

Citation (examination)
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• JP H11233723 A 19990827 - SONY CORP
• US 6086951 A 20000711 - LIN CHEN-BIN [TW], et al
• US 5825073 A 19981020 - RADOSEVICH JOSEPH RUDOLPH [US], et al
• KAR-ROY A ET AL: "HIGH DENSITY METAL INSULATOR METAL CAPACITORS USING PECVD NITRIDE FOR MIXED SIGNAL AND RF CIRCUITS", PROCEEDINGS OF THE IEEE, INTERNATIONAL INTERCONNECT TECHNOLOGYCONFERENCE, XX, XX, 24 May 1999 (1999-05-24), pages 245 - 247, XP000933962

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